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Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of [Embedded - Microprocessors](#)

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	266MHz
Co-Processors/DSP	-
RAM Controllers	DDR
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 + PHY (2)
Voltage - I/O	2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	620-BBGA Exposed Pad
Supplier Device Package	620-HBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8347vradd

- Enhanced host controller interface (EHCI) compatible
 - Complies with *USB Specification Rev. 2.0*
- High-speed (480 Mbps), full-speed (12 Mbps), and low-speed (1.5 Mbps) operations
- Direct connection to a high-speed device without an external hub
- External PHY with serial and low-pin count (ULPI) interfaces
- Local bus controller (LBC)
 - Multiplexed 32-bit address and data operating at up to 133 MHz
 - Four chip selects support four external slaves
 - Up to eight-beat burst transfers
 - 32-, 16-, and 8-bit port sizes controlled by an on-chip memory controller
 - Three protocol engines on a per chip select basis:
 - General-purpose chip select machine (GPCM)
 - Three user-programmable machines (UPMs)
 - Dedicated single data rate SDRAM controller
 - Parity support
 - Default boot ROM chip select with configurable bus width (8-, 16-, or 32-bit)
- Programmable interrupt controller (PIC)
 - Functional and programming compatibility with the MPC8260 interrupt controller
 - Support for 8 external and 35 internal discrete interrupt sources
 - Support for 1 external (optional) and 7 internal machine checkstop interrupt sources
 - Programmable highest priority request
 - Four groups of interrupts with programmable priority
 - External and internal interrupts directed to host processor
 - Redirects interrupts to external $\overline{\text{INTA}}$ pin in core disable mode.
 - Unique vector number for each interrupt source
- Dual industry-standard I²C interfaces
 - Two-wire interface
 - Multiple master support
 - Master or slave I²C mode support
 - On-chip digital filtering rejects spikes on the bus
 - System initialization data optionally loaded from I²C-1 EPROM by boot sequencer embedded hardware
- DMA controller
 - Four independent virtual channels
 - Concurrent execution across multiple channels with programmable bandwidth control
 - All channels accessible to local core and remote PCI masters
 - Misaligned transfer capability

6 DDR SDRAM

This section describes the DC and AC electrical specifications for the DDR SDRAM interface of the MPC8347E.

NOTE

The information in this document is accurate for revision 1.1 silicon and earlier. For information on revision 3.0 silicon and earlier versions see the *MPC8347EA PowerQUICC™ II Pro Integrated Host Processor Hardware Specifications*. See [Section 23.1, “Part Numbers Fully Addressed by This Document,”](#) for silicon revision level determination.

6.1 DDR SDRAM DC Electrical Characteristics

[Table 11](#) provides the recommended operating conditions for the DDR SDRAM component(s) of the MPC8347E.

Table 11. DDR SDRAM DC Electrical Characteristics

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.18$	$GV_{DD} + 0.3$	V	
Input low voltage	V_{IL}	-0.3	$MV_{REF} - 0.18$	V	
Output leakage current	I_{OZ}	-10	10	μA	4
Output high current ($V_{OUT} = 1.95$ V)	I_{OH}	-15.2	—	mA	
Output low current ($V_{OUT} = 0.35$ V)	I_{OL}	15.2	—	mA	
MV_{REF} input leakage current	I_{VREF}	—	5	μA	

Notes:

- GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
- MV_{REF} is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed $\pm 2\%$ of the DC value.
- V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF} . This rail should track variations in the DC level of MV_{REF} .
- Output leakage is measured with all outputs disabled, $0 V \leq V_{OUT} \leq GV_{DD}$.

[Table 12](#) provides the DDR capacitance.

Table 12. DDR SDRAM Capacitance

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:

- This parameter is sampled. $GV_{DD} = 2.5 V \pm 0.125 V$, $f = 1$ MHz, $T_A = 25^\circ C$, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

Table 20. RGMII/RTBI (When Operating at 2.5 V) DC Electrical Characteristics

Parameters	Symbol	Conditions		Min	Max	Unit
Supply voltage 2.5 V	V_{DD}	—		2.37	2.63	V
Output high voltage	V_{OH}	$I_{OH} = -1.0 \text{ mA}$	$V_{DD} = \text{Min}$	2.00	$V_{DD} + 0.3$	V
Output low voltage	V_{OL}	$I_{OL} = 1.0 \text{ mA}$	$V_{DD} = \text{Min}$	$\text{GND} - 0.3$	0.40	V
Input high voltage	V_{IH}	—	$V_{DD} = \text{Min}$	1.7	$V_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	$V_{DD} = \text{Min}$	-0.3	0.70	V
Input high current	I_{IH}	$V_{IN}^1 = V_{DD}$		—	10	μA
Input low current	I_{IL}	$V_{IN}^1 = \text{GND}$		-15	—	μA

Note:

1. The symbol V_{IN} , in this case, represents the V_{IN} symbol referenced in Table 1 and Table 2.

8.2 GMII, MII, TBI, RGMII, and RTBI AC Timing Specifications

The AC timing specifications for GMII, MII, TBI, RGMII, and RTBI are presented in this section.

8.2.1 GMII Timing Specifications

This section describes the GMII transmit and receive AC timing specifications.

8.2.1.1 GMII Transmit AC Timing Specifications

Table 21 provides the GMII transmit AC timing specifications.

Table 21. GMII Transmit AC Timing Specifications

At recommended operating conditions with V_{DD}/OV_{DD} of $3.3 \text{ V} \pm 10\%$.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
GTX_CLK clock period	t_{GTX}	—	8.0	—	ns
GTX_CLK duty cycle	t_{GTXH}/t_{GTX}	43.75	—	56.25	%
GTX_CLK to GMII data TXD[7:0], TX_ER, TX_EN delay	t_{GTKHDX}	0.5	—	5.0	ns
GTX_CLK clock rise time, $V_{IL}(\text{min})$ to $V_{IH}(\text{max})$	t_{GTXR}	—	—	1.0	ns
GTX_CLK clock fall time, $V_{IH}(\text{max})$ to $V_{IL}(\text{min})$	t_{GTXF}	—	—	1.0	ns
GTX_CLK125 clock period	t_{G125}^2	—	8.0	—	ns
GTX_CLK125 reference clock duty cycle measured at $V_{DD}/2$	t_{G125H}/t_{G125}	45	—	55	%

Notes:

- The symbols for timing specifications follow the pattern $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{GTKHDV} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) reaching the valid state (V) to state or setup time. Also, t_{GTKHDX} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) going invalid (X) or hold time. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{GTX} represents the GMII(G) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
- This symbol represents the external GTX_CLK125 signal and does not follow the original symbol naming convention.

Table 35. Local Bus General Timing Parameters—DLL Bypass⁹ (continued)

Parameter	Symbol ¹	Min	Max	Unit	Notes
Local bus clock to output valid	t_{LBKLOV}	—	3	ns	3
Local bus clock to output high impedance for LAD/LDP	t_{LBKHOZ}	—	4	ns	8

Notes:

- The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{LBIXKH1} symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
- All timings are in reference to the falling edge of LCLK0 (for all outputs and for $\overline{\text{LGT\bar{A}}}$ and LUPWAIT inputs) or the rising edge of LCLK0 (for all other inputs).
- All signals are measured from $OV_{\text{DD}}/2$ of the rising/falling edge of LCLK0 to $0.4 \times OV_{\text{DD}}$ of the signal in question for 3.3 V signaling levels.
- Input timings are measured at the pin.
- t_{LBOTOT1} should be used when RCWH[LALE] is not set and when the load on the LALE output pin is at least 10 pF less than the load on the LAD output pins.
- t_{LBOTOT2} should be used when RCWH[LALE] is set and when the load on the LALE output pin is at least 10 pF less than the load on the LAD output pins.
- t_{LBOTOT3} should be used when RCWH[LALE] is set and when the load on the LALE output pin equals to the load on the LAD output pins.
- For purposes of active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
- DLL bypass mode is not recommended for use at frequencies above 66 MHz.

Figure 19 provides the AC test load for the local bus.

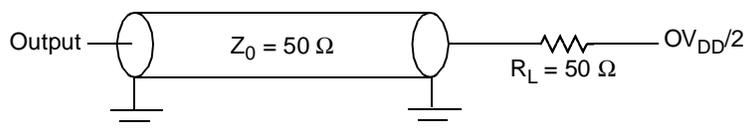


Figure 19. Local Bus C Test Load

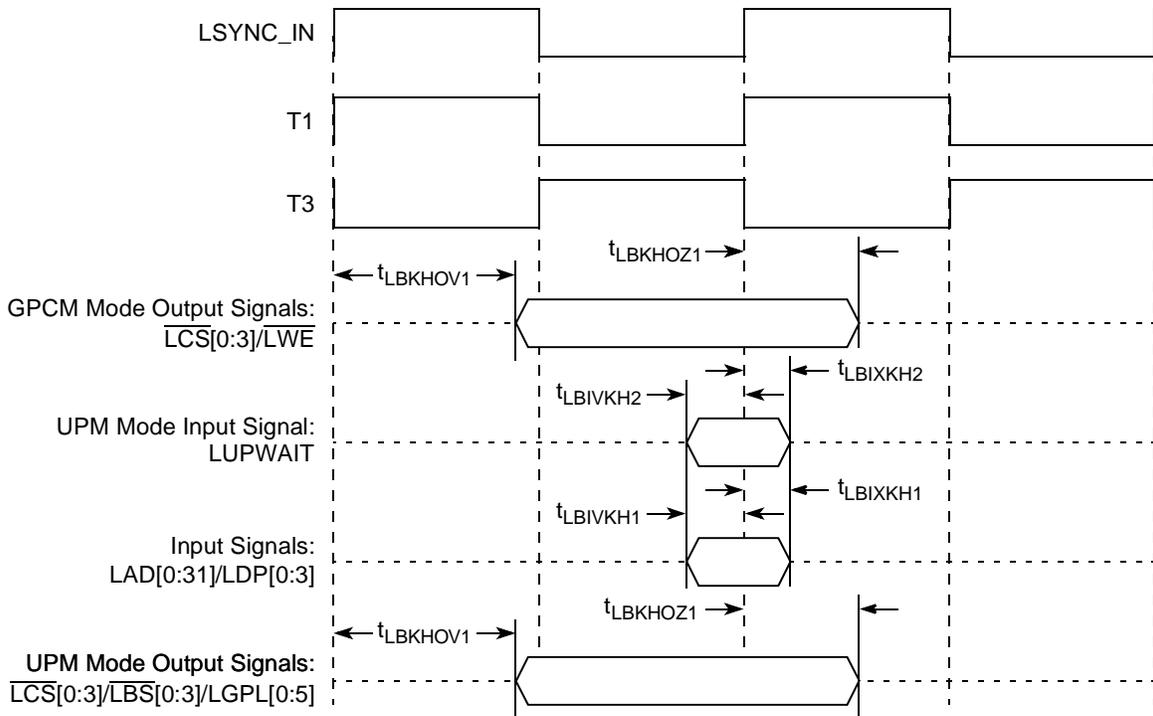


Figure 22. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 2 (DLL Enabled)

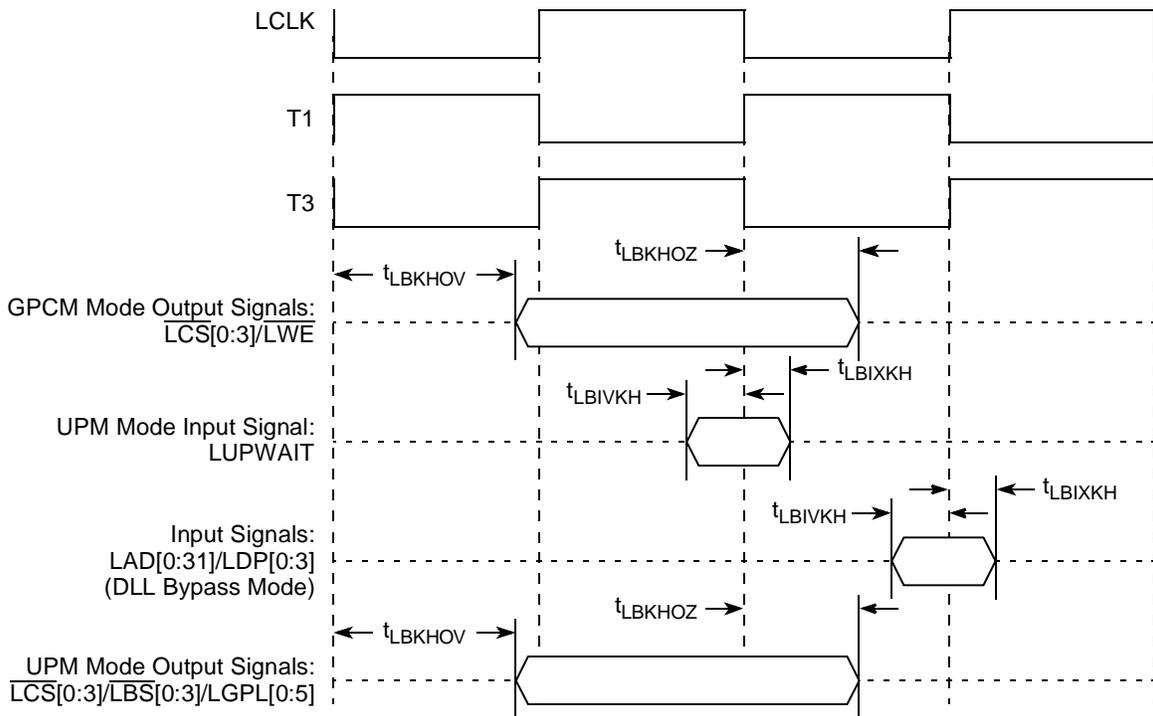


Figure 23. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 2 (DLL Bypass Mode)

11 JTAG

This section describes the DC and AC electrical specifications for the IEEE Std. 1149.1 (JTAG) interface of the MPC8347E

11.1 JTAG DC Electrical Characteristics

Table 36 provides the DC electrical characteristics for the IEEE Std. 1149.1 (JTAG) interface of the MPC8347E.

Table 36. JTAG interface DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}		$OV_{DD} - 0.3$	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}		-0.3	0.8	V
Input current	I_{IN}			±5	μA
Output high voltage	V_{OH}	$I_{OH} = -8.0$ mA	2.4	—	V
Output low voltage	V_{OL}	$I_{OL} = 8.0$ mA	—	0.5	V
Output low voltage	V_{OL}	$I_{OL} = 3.2$ mA	—	0.4	V

11.2 JTAG AC Timing Specifications

This section describes the AC electrical specifications for the IEEE Std. 1149.1 (JTAG) interface of the MPC8347E. Table 37 provides the JTAG AC timing specifications as defined in Figure 27 through Figure 30.

Table 37. JTAG AC Timing Specifications (Independent of CLKIN)¹

At recommended operating conditions (see Table 2).

Parameter	Symbol ²	Min	Max	Unit	Notes
JTAG external clock frequency of operation	f_{JTG}	0	33.3	MHz	
JTAG external clock cycle time	t_{JTG}	30	—	ns	
JTAG external clock pulse width measured at 1.4 V	t_{JTKHKL}	15	—	ns	
JTAG external clock rise and fall times	t_{JTGR}, t_{JTGF}	0	2	ns	
\overline{TRST} assert time	t_{TRST}	25	—	ns	3
Input setup times:				ns	
Boundary-scan data	t_{JTDVKH}	4	—		4
TMS, TDI	t_{JTIVKH}	4	—		
Input hold times:				ns	
Boundary-scan data	t_{JTDXKH}	10	—		4
TMS, TDI	t_{JTIXKH}	10	—		
Valid times:				ns	
Boundary-scan data	t_{JTKLDV}	2	11		5
TDO	t_{JTKLOV}	2	11		

Table 37. JTAG AC Timing Specifications (Independent of CLKIN)¹ (continued)

At recommended operating conditions (see Table 2).

Parameter	Symbol ²	Min	Max	Unit	Notes
Output hold times:				ns	
Boundary-scan data	t_{JTKLDX}	2	—		5
TDO	t_{JKLOX}	2	—		
JTAG external clock to output high impedance:				ns	
Boundary-scan data	t_{JTKLDZ}	2	19		5, 6
TDO	t_{JKLOZ}	2	9		

Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50 Ω load (see Figure 26). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{JTDVXH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. $\overline{\text{TRST}}$ is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK} .
5. Non-JTAG signal output timing with respect to t_{TCLK} .
6. Guaranteed by design and characterization.

Figure 26 provides the AC test load for TDO and the boundary-scan outputs of the MPC8347E.

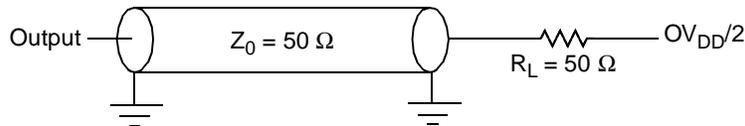


Figure 26. AC Test Load for the JTAG Interface

Figure 27 provides the JTAG clock input timing diagram.

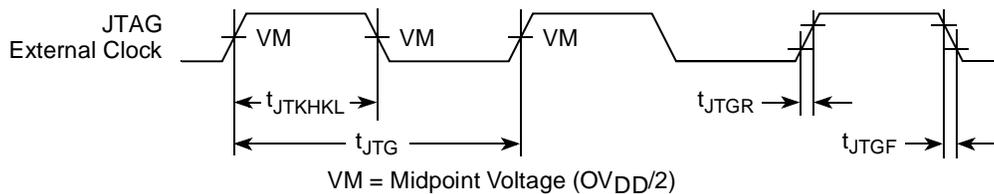


Figure 27. JTAG Clock Input Timing Diagram

13 PCI

This section describes the DC and AC electrical specifications for the PCI bus of the MPC8347E.

13.1 PCI DC Electrical Characteristics

Table 40 provides the DC electrical characteristics for the PCI interface of the MPC8347E.

Table 40. PCI DC Electrical Characteristics

Parameter	Symbol	Test Condition	Min	Max	Unit
High-level input voltage	V_{IH}	$V_{OUT} \geq V_{OH} \text{ (min) or}$	2	$OV_{DD} + 0.3$	V
Low-level input voltage	V_{IL}	$V_{OUT} \leq V_{OL} \text{ (max)}$	-0.3	0.8	V
Input current	I_{IN}	$V_{IN}^1 = 0 \text{ V or } V_{IN} = OV_{DD}$	—	± 5	μA
High-level output voltage	V_{OH}	$OV_{DD} = \text{min,}$ $I_{OH} = -100 \mu\text{A}$	$OV_{DD} - 0.2$	—	V
Low-level output voltage	V_{OL}	$OV_{DD} = \text{min,}$ $I_{OL} = 100 \mu\text{A}$	—	0.2	V

Note:

1. The symbol V_{IN} , in this case, represents the OV_{IN} symbol referenced in Table 1.

13.2 PCI AC Electrical Specifications

This section describes the general AC timing parameters of the PCI bus of the MPC8347E. Note that the PCI_CLK or PCI_SYNC_IN signal is used as the PCI input clock depending on whether the MPC8347E is configured as a host or agent device. Table 41 provides the PCI AC timing specifications at 66 MHz.

Table 41. PCI AC Timing Specifications at 66 MHz¹

Parameter	Symbol ²	Min	Max	Unit	Notes
Clock to output valid	t_{PCKHOV}	—	6.0	ns	3
Output hold from clock	t_{PCKHOX}	1	—	ns	3
Clock to output high impedance	t_{PCKHOZ}	—	14	ns	3, 4
Input setup to clock	t_{PCIVKH}	3.0	—	ns	3, 5

Table 41. PCI AC Timing Specifications at 66 MHz¹ (continued)

Parameter	Symbol ²	Min	Max	Unit	Notes
Input hold from clock	$t_{PCI\text{XKH}}$	0	—	ns	3, 5

Notes:

1. PCI timing depends on M66EN and the ratio between PCI1/PCI2. Refer to the PCI chapter of the reference manual for a description of M66EN.
2. The symbols for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{PCIVKH} symbolizes PCI timing (PC) with respect to the time the input signals (I) reach the valid state (V) relative to the PCI_SYNC_IN clock, t_{SYS} , reference (K) going to the high (H) state or setup time. Also, t_{PCRHFV} symbolizes PCI timing (PC) with respect to the time hard reset (R) went high (H) relative to the frame signal (F) going to the valid (V) state.
3. See the timing measurement conditions in the *PCI 2.2 Local Bus Specifications*.
4. For active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
5. Input timings are measured at the pin.

Table 42 provides the PCI AC timing specifications at 33 MHz.

Table 42. PCI AC Timing Specifications at 33 MHz

Parameter	Symbol ¹	Min	Max	Unit	Notes
Clock to output valid	t_{PCKHOV}	—	11	ns	2
Output hold from clock	t_{PCKHOX}	2	—	ns	2
Clock to output high impedance	t_{PCKHOZ}	—	14	ns	2, 3
Input setup to clock	t_{PCIVKH}	3.0	—	ns	2, 4
Input hold from clock	$t_{PCI\text{XKH}}$	0	—	ns	2, 4

Notes:

1. The symbols for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{PCIVKH} symbolizes PCI timing (PC) with respect to the time the input signals (I) reach the valid state (V) relative to the PCI_SYNC_IN clock, t_{SYS} , reference (K) going to the high (H) state or setup time. Also, t_{PCRHFV} symbolizes PCI timing (PC) with respect to the time hard reset (R) went high (H) relative to the frame signal (F) going to the valid (V) state.
2. See the timing measurement conditions in the *PCI 2.2 Local Bus Specifications*.
3. For active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
4. Input timings are measured at the pin.

Figure 33 provides the AC test load for PCI.

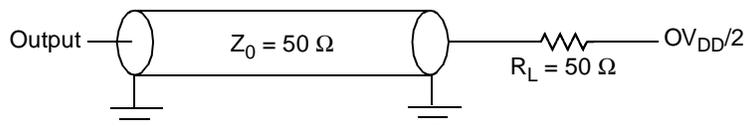


Figure 33. PCI AC Test Load

14 Timers

This section describes the DC and AC electrical specifications for the timers.

14.1 Timer DC Electrical Characteristics

Table 43 provides the DC electrical characteristics for the MPC8347E timer pins, including $\overline{\text{TIN}}$, $\overline{\text{TOUT}}$, $\overline{\text{TGATE}}$, and $\overline{\text{RTC_CLK}}$.

Table 43. Timer DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}		2.0	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}		-0.3	0.8	V
Input current	I_{IN}			± 5	μA
Output high voltage	V_{OH}	$I_{OH} = -8.0 \text{ mA}$	2.4	—	V
Output low voltage	V_{OL}	$I_{OL} = 8.0 \text{ mA}$	—	0.5	V
Output low voltage	V_{OL}	$I_{OL} = 3.2 \text{ mA}$	—	0.4	V

14.2 Timer AC Timing Specifications

Table 44 provides the timer input and output AC timing specifications.

Table 44. Timers Input AC Timing Specifications¹

Characteristic	Symbol ²	Min	Unit
Timers inputs—minimum pulse width	t_{TWID}	20	ns

Notes:

1. Input specifications are measured from the 50 percent level of the signal to the 50 percent level of the rising edge of CLKIN. Timings are measured at the pin.
2. Timer inputs and outputs are asynchronous to any visible clock. Timer outputs should be synchronized before use by external synchronous logic. Timer inputs are required to be valid for at least t_{TWID} ns to ensure proper operation.

18.5 Pinout Listings

Table 51 provides the pinout listing for the MPC8347E, 672 TBGA package.

Table 51. MPC8347E (TBGA) Pinout Listing

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI				
$\overline{\text{PCI_INTA/IRQ_OUT}}$	B34	O	OV_{DD}	2
$\overline{\text{PCI_RESET_OUT}}$	C33	O	OV_{DD}	
PCI_AD[31:0]	G30, G32, G34, H31, H32, H33, H34, J29, J32, J33, L30, K31, K33, K34, L33, L34, P34, R29, R30, R33, R34, T31, T32, T33, U31, U34, V31, V32, V33, V34, W33, W34	I/O	OV_{DD}	
PCI_C $\overline{\text{BE}}$ [3:0]	J30, M31, P33, T34	I/O	OV_{DD}	
PCI_PAR	P32	I/O	OV_{DD}	
$\overline{\text{PCI_FRAME}}$	M32	I/O	OV_{DD}	5
$\overline{\text{PCI_TRDY}}$	N29	I/O	OV_{DD}	5
$\overline{\text{PCI_IRDY}}$	M34	I/O	OV_{DD}	5
$\overline{\text{PCI_STOP}}$	N31	I/O	OV_{DD}	5
$\overline{\text{PCI_DEVSEL}}$	N30	I/O	OV_{DD}	5
PCI_IDSEL	J31	I	OV_{DD}	
$\overline{\text{PCI_SERR}}$	N34	I/O	OV_{DD}	5
$\overline{\text{PCI_PERR}}$	N33	I/O	OV_{DD}	5
$\overline{\text{PCI_REQ}}[0]$	D32	I/O	OV_{DD}	
$\overline{\text{PCI_REQ}}[1]/\text{CPCI1_HS_ES}$	D34	I	OV_{DD}	
$\overline{\text{PCI_REQ}}[2:4]$	E34, F32, G29	I	OV_{DD}	
$\overline{\text{PCI_GNT0}}$	C34	I/O	OV_{DD}	
$\overline{\text{PCI_GNT1}}/\text{CPCI1_HS_LED}$	D33	O	OV_{DD}	
$\overline{\text{PCI_GNT2}}/\text{CPCI1_HS_ENUM}$	E33	O	OV_{DD}	
$\overline{\text{PCI_GNT}}[3:4]$	F31, F33	O	OV_{DD}	
M66EN	A19	I	OV_{DD}	
DDR SDRAM Memory Interface				
MDQ[0:63]	D5, A3, C3, D3, C4, B3, C2, D4, D2, E5, G2, H6, E4, F3, G4, G3, H1, J2, L6, M6, H2, K6, L2, M4, N2, P4, R2, T4, P6, P3, R1, T2, AB5, AA3, AD6, AE4, AB4, AC2, AD3, AE6, AE3, AG4, AK5, AK4, AE2, AG6, AK3, AK2, AL2, AL1, AM5, AP5, AM2, AN1, AP4, AN5, AJ7, AN7, AM8, AJ9, AP6, AL7, AL9, AN8	I/O	GV_{DD}	

Table 51. MPC8347E (TBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
System Control				
$\overline{\text{PORESET}}$	C18	I	OV_{DD}	
$\overline{\text{HRESET}}$	B18	I/O	OV_{DD}	1
$\overline{\text{SRESET}}$	D18	I/O	OV_{DD}	2
Thermal Management				
THERM0	K32	I	—	9
Power and Ground Signals				
$\text{AV}_{\text{DD}1}$	L31	Power for e300 PLL (1.2 V)	$\text{AV}_{\text{DD}1}$	
$\text{AV}_{\text{DD}2}$	AP12	Power for system PLL (1.2 V)	$\text{AV}_{\text{DD}2}$	
$\text{AV}_{\text{DD}3}$	AE1	Power for DDR DLL (1.2 V)	$\text{AV}_{\text{DD}3}$	
$\text{AV}_{\text{DD}4}$	AJ13	Power for LBIU DLL (1.2 V)	$\text{AV}_{\text{DD}4}$	
GND	A1, A34, C1, C7, C10, C11, C15, C23, C25, C28, D1, D8, D20, D30, E7, E13, E15, E17, E18, E21, E23, E25, E32, F6, F19, F27, F30, F34, G31, H5, J4, J34, K30, L5, M2, M5, M30, M33, N3, N5, P30, R5, R32, T5, T30, U6, U29, U33, V2, V5, V30, W6, W30, Y30, AA2, AA30, AB2, AB6, AB30, AC3, AC6, AD31, AE5, AF2, AF5, AF31, AG30, AG31, AH4, AJ3, AJ19, AJ22, AK7, AK13, AK14, AK16, AK18, AK20, AK25, AK28, AL3, AL5, AL10, AL12, AL22, AL27, AM1, AM6, AM7, AN12, AN17, AN34, AP1, AP8, AP34	—	—	
GV_{DD}	A2, E2, G5, G6, J5, K4, K5, L4, N4, P5, R6, T6, U5, V1, W5, Y5, AA4, AB3, AC4, AD5, AF3, AG5, AH2, AH5, AH6, AJ6, AK6, AK8, AK9, AL6	Power for DDR DRAM I/O voltage (2.5 V)	GV_{DD}	
$\text{LV}_{\text{DD}1}$	C9, D11	Power for three-speed Ethernet #1 and for Ethernet management interface I/O (2.5 V, 3.3 V)	$\text{LV}_{\text{DD}1}$	

Table 54 provides the operating frequencies for the MPC8347E TBGA under recommended operating conditions (see Table 2).

Table 54. Operating Frequencies for TBGA

Characteristic ¹	400 MHz	533 MHz	667 MHz	Unit
e300 core frequency (<i>core_clk</i>)	266–400	266–533	266–667	MHz
Coherent system bus frequency (<i>csb_clk</i>)	100–266	100–266	100–333	MHz
DDR and memory bus frequency (MCLK) ²	100–133	100–133	100–166.67	MHz
Local bus frequency (LCLK _n) ³	16.67–133	16.67–133	16.67–133	MHz
PCI input frequency (CLKIN or PCI_CLK)	25–66	25–66	25–66	MHz
Security core maximum internal operating frequency	133	133	166	MHz
USB_DR, USB_MPH maximum internal operating frequency	133	133	166	MHz

¹ The CLKIN frequency, RCWL[SPMF], and RCWL[COREPLL] settings must be chosen so that the resulting *csb_clk*, MCLK, LCLK[0:2], and *core_clk* frequencies do not exceed their respective maximum or minimum operating frequencies. The value of SCCR[ENCCM], SCCR[USBDRCM], and SCCR[USBMPHCM] must be programmed so that the maximum internal operating frequency of the Security core and USB modules does not exceed the respective values listed in this table.

² The DDR data rate is 2x the DDR memory bus frequency.

³ The local bus frequency is 1/2, 1/4, or 1/8 of the *lbiu_clk* frequency (depending on LCCR[CLKDIV]) which is in turn 1x or 2x the *csb_clk* frequency (depending on RCWL[LBIUCM]).

Table 55 provides the operating frequencies for the MPC8347E PBGA under recommended operating conditions.

Table 55. Operating Frequencies for PBGA

Characteristic ¹	266 MHz	333 MHz	400 MHz	Unit
e300 core frequency (<i>core_clk</i>)	200–266	200–333	200–400	MHz
Coherent system bus frequency (<i>csb_clk</i>)	100–266			MHz
Local bus frequency (LCLK _n) ²	16.67–133			MHz
PCI input frequency (CLKIN or PCI_CLK)	25–66			MHz
Security core maximum internal operating frequency	133			MHz
USB_DR, USB_MPH maximum internal operating frequency	133			MHz

¹ The CLKIN frequency, RCWL[SPMF], and RCWL[COREPLL] settings must be chosen so that the resulting *csb_clk*, MCLK, LCLK[0:2], and *core_clk* frequencies do not exceed their respective maximum or minimum operating frequencies. The value of SCCR[ENCCM], SCCR[USBDRCM], and SCCR[USBMPHCM] must be programmed so that the maximum internal operating frequency of the Security core and USB modules does not exceed the respective values listed in this table.

² The local bus frequency is 1/2, 1/4, or 1/8 of the *lbiu_clk* frequency (depending on LCCR[CLKDIV]) which is in turn 1x or 2x the *csb_clk* frequency (depending on RCWL[LBIUCM]).

19.1 System PLL Configuration

The system PLL is controlled by the RCWL[SPMF] parameter. [Table 56](#) shows the multiplication factor encodings for the system PLL.

Table 56. System PLL Multiplication Factors

RCWL[SPMF]	System PLL Multiplication Factor
0000	× 16
0001	Reserved
0010	× 2
0011	× 3
0100	× 4
0101	× 5
0110	× 6
0111	× 7
1000	× 8
1001	× 9
1010	× 10
1011	× 11
1100	× 12
1101	× 13
1110	× 14
1111	× 15

As described in [Section 19, “Clocking,”](#) the LBIUCM, DDRCM, and SPMF parameters in the reset configuration word low and the CFG_CLKIN_DIV configuration input signal select the ratio between the primary clock input (CLKIN or PCI_CLK) and the internal coherent system bus clock (*csb_clk*). [Table 57](#) and [Table 58](#) show the expected frequency values for the CSB frequency for select *csb_clk* to CLKIN/PCI_SYNC_IN ratios.

Table 57. CSB Frequency Options for Host Mode

CFG_CLKIN_DIV at Reset ¹	SPMF	csb_clk : Input Clock Ratio ²	Input Clock Frequency (MHz) ²					
			16.67	25	33.33	66.67		
			csb_clk Frequency (MHz)					
Low	0010	2 : 1				133		
Low	0011	3 : 1				100	200	
Low	0100	4 : 1				100	133	266
Low	0101	5 : 1				125	166	333
Low	0110	6 : 1	100	150	200			
Low	0111	7 : 1	116	175	233			
Low	1000	8 : 1	133	200	266			
Low	1001	9 : 1	150	225	300			
Low	1010	10 : 1	166	250	333			
Low	1011	11 : 1	183	275				
Low	1100	12 : 1	200	300				
Low	1101	13 : 1	216	325				
Low	1110	14 : 1	233					
Low	1111	15 : 1	250					
Low	0000	16 : 1	266					
High	0010	2 : 1				133		
High	0011	3 : 1				100	200	
High	0100	4 : 1				133	266	
High	0101	5 : 1				166	333	
High	0110	6 : 1				200		
High	0111	7 : 1				233		
High	1000	8 : 1						

¹ CFG_CLKIN_DIV selects the ratio between CLKIN and PCI_SYNC_OUT.

² CLKIN is the input clock in host mode; PCI_CLK is the input clock in agent mode.

DDR2 memory may be used at 133 MHz provided that the memory components are specified for operation at this frequency.

20 Thermal

This section describes the thermal specifications of the MPC8347E.

20.1 Thermal Characteristics

[Table 61](#) provides the package thermal characteristics for the 672 35 × 35 mm TBGA of the MPC8347E.

Table 61. Package Thermal Characteristics for TBGA

Characteristic	Symbol	Value	Unit	Notes
Junction-to-ambient natural convection on single-layer board (1s)	$R_{\theta JA}$	14	°C/W	1, 2
Junction-to-ambient natural convection on four-layer board (2s2p)	$R_{\theta JMA}$	11	°C/W	1, 3
Junction-to-ambient (@ 200 ft/min) on single-layer board (1s)	$R_{\theta JMA}$	11	°C/W	1, 3
Junction-to-ambient (@ 200 ft/min) on four-layer board (2s2p)	$R_{\theta JMA}$	8	°C/W	1, 3
Junction-to-ambient (@ 2 m/s) on single-layer board (1s)	$R_{\theta JMA}$	9	°C/W	1, 3
Junction-to-ambient (@ 2 m/s) on four-layer board (2s2p)	$R_{\theta JMA}$	7	°C/W	1, 3
Junction-to-board thermal	$R_{\theta JB}$	3.8	°C/W	4
Junction-to-case thermal	$R_{\theta JC}$	1.7	°C/W	5
Junction-to-package natural convection on top	Ψ_{JT}	1	°C/W	6

Notes:

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Per SEMI G38-87 and JEDEC JESD51-2 with the single-layer board horizontal.
3. Per JEDEC JESD51-6 with the board horizontal, 1 m/s is approximately equal to 200 linear feet per minute (LFM).
4. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

[Table 62](#) provides the package thermal characteristics for the 620 29 × 29 mm PBGA of the MPC8347E.

Table 62. Package Thermal Characteristics for PBGA

Characteristic	Symbol	Value	Unit	Notes
Junction-to-ambient natural convection on single-layer board (1s)	$R_{\theta JA}$	21	°C/W	1, 2
Junction-to-ambient natural convection on four-layer board (2s2p)	$R_{\theta JMA}$	15	°C/W	1, 3
Junction-to-ambient (@ 200 ft/min) on single-layer board (1s)	$R_{\theta JMA}$	17	°C/W	1, 3
Junction-to-ambient (@ 200 ft/min) on four-layer board (2s2p)	$R_{\theta JMA}$	12	°C/W	1, 3
Junction-to-board thermal	$R_{\theta JB}$	6	°C/W	4

Table 62. Package Thermal Characteristics for PBGA (continued)

Characteristic	Symbol	Value	Unit	Notes
Junction-to-case thermal	$R_{\theta JC}$	5	°C/W	5
Junction-to-package natural convection on top	Ψ_{JT}	5	°C/W	6

Notes

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Per SEMI G38-87 and JEDEC JESD51-2 with the single-layer board horizontal.
3. Per JEDEC JESD51-6 with the board horizontal.
4. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

20.2 Thermal Management Information

For the following sections, $P_D = (V_{DD} \times I_{DD}) + P_{I/O}$ where $P_{I/O}$ is the power dissipation of the I/O drivers. See [Table 5](#) for I/O power dissipation values.

20.2.1 Estimation of Junction Temperature with Junction-to-Ambient Thermal Resistance

An estimation of the chip junction temperature, T_J , can be obtained from the equation:

$$T_J = T_A + (R_{\theta JA} \times P_D)$$

where:

T_J = junction temperature (°C)

T_A = ambient temperature for the package (°C)

$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)

P_D = power dissipation in the package (W)

The junction-to-ambient thermal resistance is an industry-standard value that provides a quick and easy estimation of thermal performance. Generally, the value obtained on a single-layer board is appropriate for a tightly packed printed-circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated. Test cases have demonstrated that errors of a factor of two (in the quantity $T_J - T_A$) are possible.

20.2.2 Estimation of Junction Temperature with Junction-to-Board Thermal Resistance

The thermal performance of a device cannot be adequately predicted from the junction-to-ambient thermal resistance. The thermal performance of any component is strongly dependent on the power dissipation of surrounding components. In addition, the ambient temperature varies widely within the application. For

many natural convection and especially closed box applications, the board temperature at the perimeter (edge) of the package is approximately the same as the local air temperature near the device. Specifying the local ambient conditions explicitly as the board temperature provides a more precise description of the local ambient conditions that determine the temperature of the device.

At a known board temperature, the junction temperature is estimated using the following equation:

$$T_J = T_A + (R_{\theta JA} \times P_D)$$

where:

T_J = junction temperature (°C)

T_A = ambient temperature for the package (°C)

$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)

P_D = power dissipation in the package (W)

When the heat loss from the package case to the air can be ignored, acceptable predictions of junction temperature can be made. The application board should be similar to the thermal test condition: the component is soldered to a board with internal planes.

20.2.3 Experimental Determination of Junction Temperature

To determine the junction temperature of the device in the application after prototypes are available, use the thermal characterization parameter (Ψ_{JT}) to determine the junction temperature and a measure of the temperature at the top center of the package case using the following equation:

$$T_J = T_T + (\Psi_{JT} \times P_D)$$

where:

T_J = junction temperature (°C)

T_T = thermocouple temperature on top of package (°C)

Ψ_{JT} = junction-to-ambient thermal resistance (°C/W)

P_D = power dissipation in the package (W)

The thermal characterization parameter is measured per the JESD51-2 specification using a 40 gauge type T thermocouple epoxied to the top center of the package case. The thermocouple should be positioned so that the thermocouple junction rests on the package. A small amount of epoxy is placed over the thermocouple junction and over about 1 mm of wire extending from the junction. The thermocouple wire is placed flat against the package case to avoid measurement errors caused by cooling effects of the thermocouple wire.

20.2.4 Heat Sinks and Junction-to-Case Thermal Resistance

Some application environments require a heat sink to provide the necessary thermal management of the device. When a heat sink is used, the thermal resistance is expressed as the sum of a junction-to-case thermal resistance and a case-to-ambient thermal resistance:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$$

21.3 Decoupling Recommendations

Due to large address and data buses and high operating frequencies, the MPC8347E can generate transient power surges and high frequency noise in its power supply, especially while driving large capacitive loads. This noise must be prevented from reaching other components in the MPC8347E system, and the MPC8347E itself requires a clean, tightly regulated source of power. Therefore, the system designer should place at least one decoupling capacitor at each V_{DD} , OV_{DD} , GV_{DD} , and LV_{DD} pin of the MPC8347E. These capacitors should receive their power from separate V_{DD} , OV_{DD} , GV_{DD} , LV_{DD} , and GND power planes in the PCB, with short traces to minimize inductance. Capacitors can be placed directly under the device using a standard escape pattern. Others can surround the part.

These capacitors should have a value of 0.01 or 0.1 μF . Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

In addition, distribute several bulk storage capacitors around the PCB, feeding the V_{DD} , OV_{DD} , GV_{DD} , and LV_{DD} planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors should have a low ESR (equivalent series resistance) rating to ensure the quick response time. They should also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors are 100–330 μF (AVX TPS tantalum or Sanyo OSCON).

21.4 Connection Recommendations

To ensure reliable operation, connect unused inputs to an appropriate signal level. Unused active low inputs should be tied to OV_{DD} , GV_{DD} , or LV_{DD} as required. Unused active high inputs should be connected to GND. All NC (no-connect) signals must remain unconnected.

Power and ground connections must be made to all external V_{DD} , GV_{DD} , LV_{DD} , OV_{DD} , and GND pins of the MPC8347E.

21.5 Output Buffer DC Impedance

The MPC8347E drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I^2C).

To measure Z_0 for the single-ended drivers, an external resistor is connected from the chip pad to OV_{DD} or GND. Then the value of each resistor is varied until the pad voltage is $OV_{DD}/2$ (see [Figure 43](#)). The output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open) and R_P is trimmed until the voltage at the pad equals $OV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N)/2$.

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